**ON Semiconductor** 

Is Now

# Onsemi

To learn more about onsemi<sup>™</sup>, please visit our website at <u>www.onsemi.com</u>

onsemi and ONSEMI: and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product factures, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application is the human body. Should Buyer purchase or use onsemi products for any such unintended or unauthorized application, Buyer shall indemnify and hold onsemi and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application, Buyer shall indemnify and hold ons

## **MOSFET** – Power, Dual, N-Channel, for 1-Cell Lithium-ion Battery Protection

## 12 V, 2.85 mΩ, 20 A

This Power MOSFET features a low on-state resistance. This device is suitable for applications such as power switches of portable machines. Best suited for 1–cell lithium-ion battery applications.

#### Features

- 2.5 V Drive
- Common-Drain Type
- ESD Diode-Protected Gate
- This device is Pb-Free, Halogen Free and RoHS Compliance

#### Applications

• 1-Cell Lithium-ion Battery Charging and Discharging Switch

#### Specifications

#### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25°C)

Parameter	Symbol	Value	Unit
Source to Source Voltage	V <sub>SSS</sub>	12	V
Gate to Source Voltage	V <sub>GSS</sub>	±8	V
Source Current (DC)	۱ <sub>S</sub>	20	А
Source Current (Pulse) PW $\leq$ 10 $\mu$ s, duty cycle $\leq$ 1%	I <sub>SP</sub>	80	A
Total Dissipation (Note 1)	PT	1.8	W
Junction Temperature	Tj	150	°C
Storage Temperature	T <sub>stg</sub>	–55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction to Ambient (Note 1)	$R_{\thetaJA}$	69.4	°C/W

1. Surface mounted on ceramic substrate (5000  $\text{mm}^2 \times 0.8 \text{ mm}).$ 

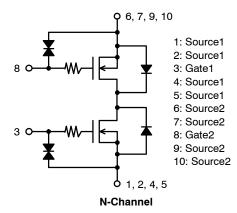


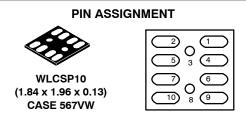
### **ON Semiconductor®**

#### www.onsemi.com

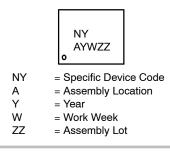
V <sub>SSS</sub>	R <sub>SS(ON)</sub> MAX	I <sub>S</sub> MAX
12 V	2.85 mΩ @ 4.5 V	20 A
	3.1 mΩ @ 3.8 V	
	4.7 mΩ @ 3.1 V	
	6.8 mΩ @ 2.5 V	

#### **ELECTRICAL CONNECTION**





#### MARKING DIAGRAM



#### ORDERING INFORMATION

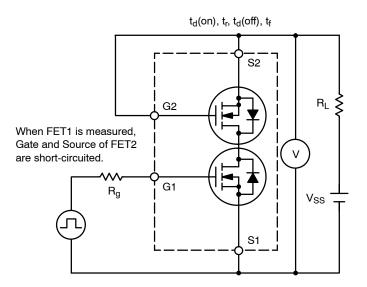
See detailed ordering and shipping information on page 2 of this data sheet.

Downloaded from Arrow.com.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>(BR)SSS</sub>	Source to Source Breakdown Voltage	e I <sub>S</sub> = 1 mA, V <sub>GS</sub> = 0 V	12			V
I <sub>SSS</sub>	Zero-Gate Voltage Source Current	V <sub>SS</sub> = 10 V, V <sub>GS</sub> = 0 V			1	μA
I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{GS} = \pm 8 \text{ V}, \text{ V}_{SS} = 0 \text{ V}$			±1	μΑ
V <sub>GS</sub> (th)	Gate Threshold Voltage	V <sub>SS</sub> = 6 V, I <sub>S</sub> = 1 mA	0.4		1.3	V
R <sub>SS</sub> (on)	(on) Static Source to Source On-State Resistance	$I_{S} = 5 \text{ A}, V_{GS} = 4.5 \text{ V}$	1.5	2.2	2.85	mΩ
F		$I_{S} = 5 \text{ A}, V_{GS} = 3.8 \text{ V}$	1.65	2.4	3.1	mΩ
		$I_{S} = 5 \text{ A}, V_{GS} = 3.1 \text{ V}$	1.9	2.8	4.7	mΩ
		$I_{\rm S}$ = 5 A, $V_{\rm GS}$ = 2.5 V	2.0	3.3	6.8	mΩ
t <sub>d</sub> (on)	Turn-ON Delay Time	$V_{SS} = 5 V, V_{GS} = 3.8 V, I_{S} = 5 A$		11		μs
t <sub>r</sub>	Rise Time	$Rg = 10 k\Omega$ Switching Test Circuit		36		μs
t <sub>d</sub> (off)	Turn-OFF Delay Time	7		95		μs
t <sub>f</sub>	Fall Time	7		70		μs
Qg	Total Gate Charge	$V_{SS}$ = 5 V, $V_{GS}$ = 3.8 V, $I_{S}$ = 5 A		30		nC
V <sub>F(S-S)</sub>	Forward Source to Source Voltage	I <sub>S</sub> = 3 A, V <sub>GS</sub> = 0 V		0.75	1.2	V

#### **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ )

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.





#### **ORDERING INFORMATION**

Device	Marking	Package	Shipping <sup>†</sup> (Qty / Packing)
EFC2K107NUZTCG	NY	WLCSOP10, 1.84 x 1.96 x 0.13 (Pb-Free / Halogen Free)	5,000 / Tape & Reel

+ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### **TYPICAL CHARACTERISTICS**

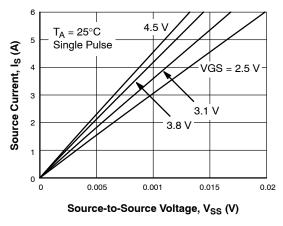
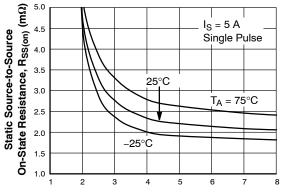


Figure 2. On-Region Characteristics



Gate-to-Source Voltage, V<sub>GS</sub> (V)

Figure 4. On-Resistance vs. Gate-to-Source Voltage

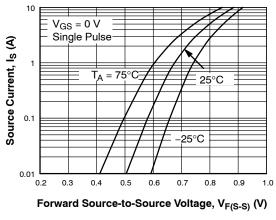


Figure 6. Forward Source-to-Source Voltage vs. Current

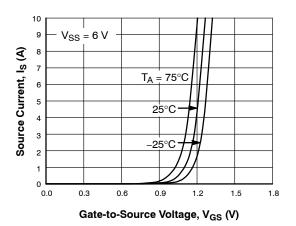
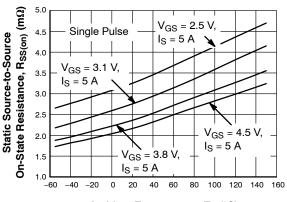


Figure 3. Transfer Characteristics



Ambient Temperature, T<sub>A</sub> (°C)



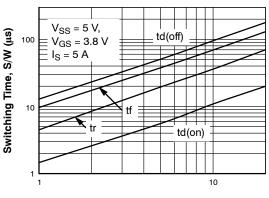




Figure 7. Switching Time vs. Gate Resistance

#### **TYPICAL CHARACTERISTICS**

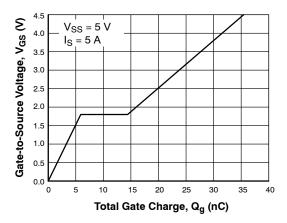


Figure 8. Gate-to-Source Voltage vs. Total Charge

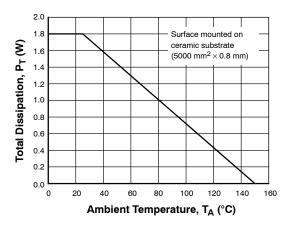


Figure 10. Total Dissipation vs. Temperature

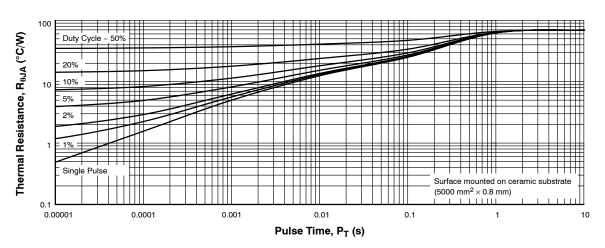


Figure 11. Thermal Response

Note on Usage: Since the EFC2K107NUZ is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

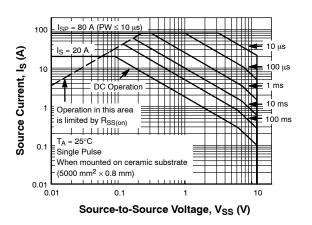
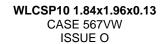
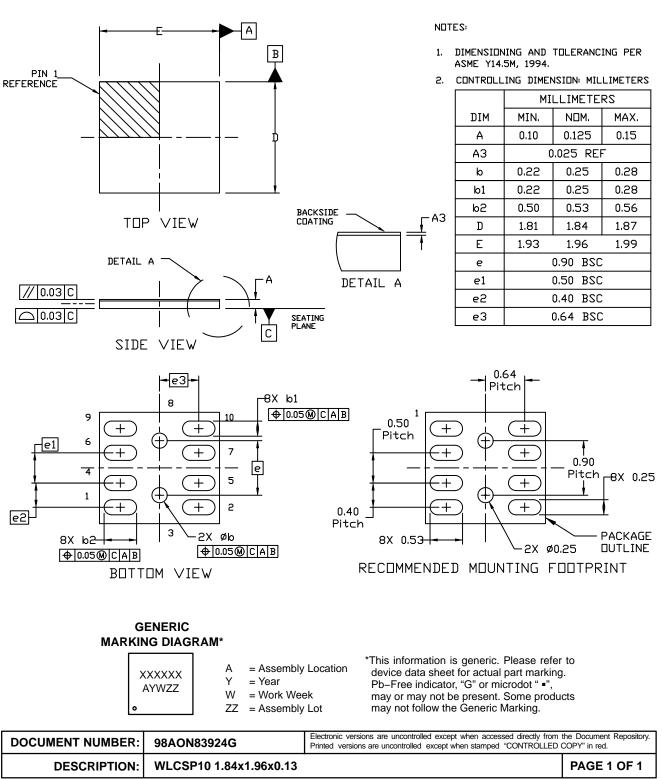


Figure 9. Safe Operating Area





DATE 28 FEB 2018



ON Semiconductor and use trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

© Semiconductor Components Industries, LLC, 2018

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor and the support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconducts harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized claim alleges that

#### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT: Email Requests to: orderlit@onsemi.com

#### TECHNICAL SUPPORT

ON Semiconductor Website: www.onsemi.com

#### North American Technical Support: Voice Mail: 1 800–282–9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support: Phone: 00421 33 790 2910 For additional information, please contact your local Sales Representative

٥